MA159A

Silicon epitaxial planer type

For switching circuits

■ Features

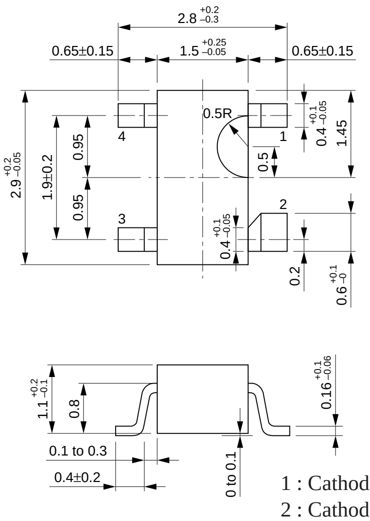
- ● Independent incorporating of two elements, enabling high-density mounting
- ● Short reverse recovery period t_{rr}
- ● Small capacity between pins, C_t

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter		Symbol	Rating	Unit
Reverse voltage (DC)		V_R	80	V
Repetitive peak reverse voltage		V_{RRM}	80	V
Average forward current	Single	$I_{F\,(AV)}$	100	mA
	Double	$I_{F\,(AV)}$	75	mA/Unit
Repetitive peak forward current	Single	I_{FRM}	225	mA
	Double	I_{FRM}	170	mA/Unit
Non-repetitive peak forward surge current	Single	I_{FSM} *	500	mA
	Double	I_{FSM} *	375	mA/Unit
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	– 55 to +150	˚C

* t=1s

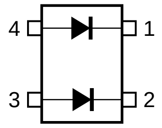
Unit : mm



1 : Cathode 1
2 : Cathode 2
3 : Anode 2
4 : Anode 1
Mini Type Package (4-pin)

Marking Symbol : M1B

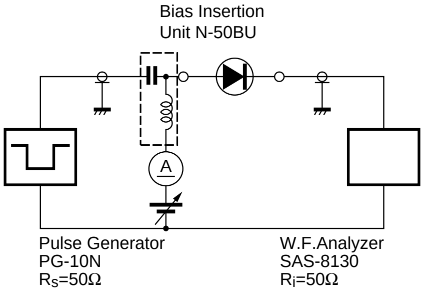
■ Internal Connection

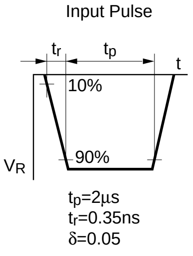


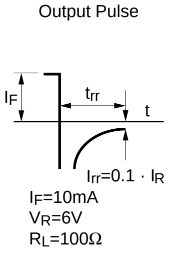
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 75V			0.1	µA
Forward voltage (DC)	V_F	I_F=100mA		0.95	1.2	V
Reverse voltage (DC)	V_R	I_R=100µA	80			V
Terminal capacitance	C_t	V_R= 0V, f=1MHz		0.9	2	pF
Reverse recovery time	t_{rr} *	I_F=10mA, V_R= 6V I_{rr}= 0.1 · I_R, R_L=100Ω			3	ns

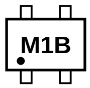
Note 1 : Rated input/output frequency : 100MHz
2 : * t_{rr} measuring circuit



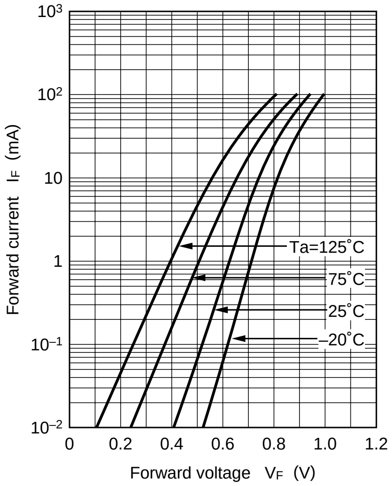




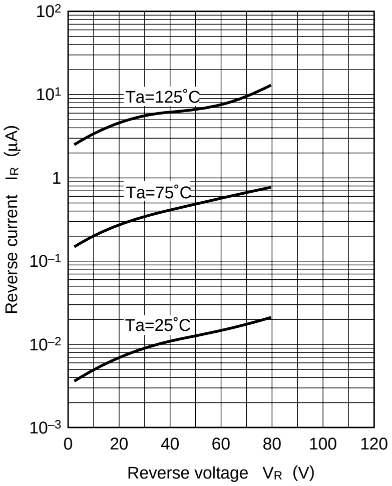
■ Marking



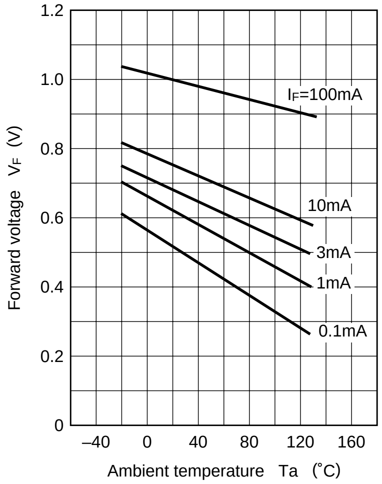
$I_F – V_F$



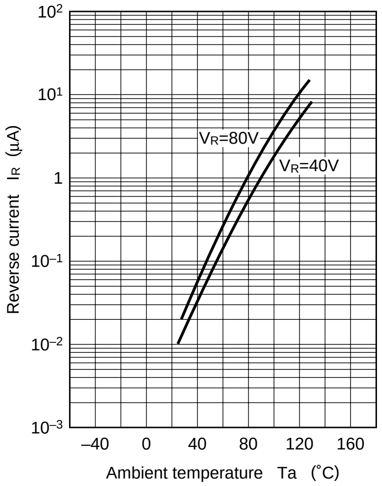
$I_R – V_R$



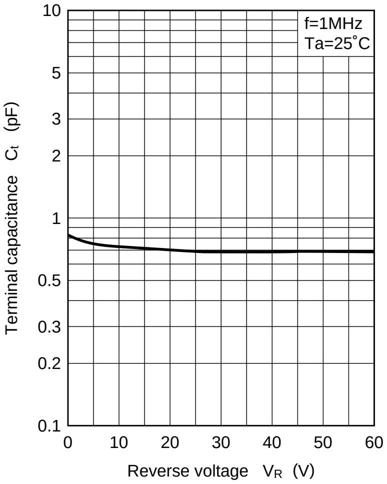
$V_F – Ta$



$I_R – Ta$



$C_t – V_R$



$I_{F\ (surge)} – t_W$